

### **INCHANGE SEMICONDUCTOR**

1 2 3

\*\* uQ

E

Ó

DIM

А

В

С

D

E

F

G

Н

J Κ

Ν

0

R

s

U

Y

# isc N-Channel MOSFET Transistor

## 2SK1757

pin 1, Gate

G

R -

mm

15.50 15.70

MAX 19.60 20.30

4.90

1.10

.60

3.20

40

0.605

2 20

5.10

3.45

2.100

6.20 9.90 | 10.10

MIN

4.70

0.90

3.40

2.90

3.20

.595

4.90

3.35

5.90

1.995

19.80 20.70 1.90

10.89 10.91

90

С S 2, Drain

3. Source TO-3PN package

### **FEATURES**

- Drain Current –I<sub>D</sub>= 15A@ T<sub>C</sub>=25℃
- · Drain Source Voltage-: V<sub>DSS</sub>= 500V(Min)
- Static Drain-Source On-Resistance
- :  $R_{DS(on)} = 0.6 \Omega$  (Max)
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRIPTION

• motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS(Ta=25 C)						
SYMBOL	PARAMETER VALUE		UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	500	V			
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±30	V			
ID	Drain Current-Continuous	±15	A			
I <sub>DM</sub>	Drain Current-Single Pluse	±60	А			
PD	Total Dissipation @Tc=25℃	120	W			
TJ	Max. Operating Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			
		L				

### ABSOLUTE MAXIMUM RATINGS(T\_=25°C

## isc website: www.iscsemi.com

PARAMETER

Thermal Resistance, Junction to Case

THERMAL CHARACTERISTICS

SYMBOL

Rth j-c



MAX

1.04

UNIT

°C/W



## isc N-Channel MOSFET Transistor

### 2SK1757

#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0;	500		V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> = 1mA	2.5	3.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 8A		0.6	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0		±10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500V; V <sub>GS</sub> = 0		100	uA
Vsd	Forward On-Voltage	I <sub>E</sub> = 15A; V <sub>GS</sub> = 0		1	V

#### NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.